

Finding the crystal axes

in an n-type segmented germanium detector

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Particle Physics School Munich Colloquium

Munich, January **Friday 13**, 2012



MAX-PLANCK-GESellschaft

Submitted to EPJ C
arXiv:1112.5291 [nucl-ex]



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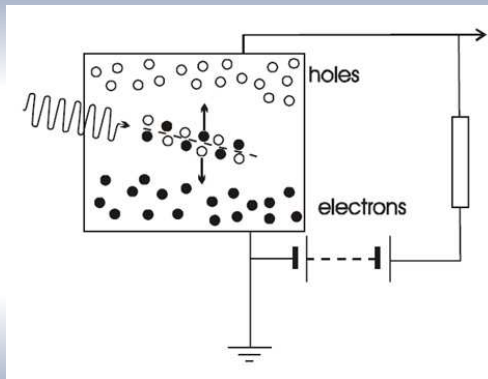
Outline

- Introduction: germanium detectors
- Anisotropy in germanium crystals
- Experimental setup and simulation
- The method to extraction the axes orientation
- Results, comparison and variations of the method
- Summary



Introduction

Semiconductor detectors are used to register radiation:



Germanium detectors

Germanium detectors have a very good energy resolution:
4-7 keV @ 2 MeV. They are used for:

- Spectroscopy, to measure low levels of radioactivity;
- Gamma ray tracking;
- $0\nu\beta\beta$ experiments: source=detector approach with detectors enriched in ^{68}Ge which $\beta\beta$ decays;
- ...



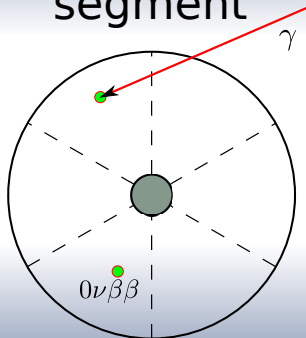
Analysis techniques for $0\nu\beta\beta$ with Ge detectors

- Detector granularity: **segmentation** helps to distinguish single-segment events (signal) from multi-segment events (background) and to localize events;
- Analysis of pulse shapes: collected charge pulses differ depending on event topology; **simulation** may be involved.

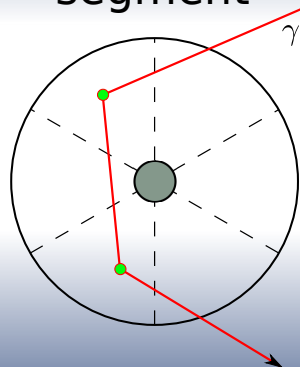


Segmentation: background rejection technique

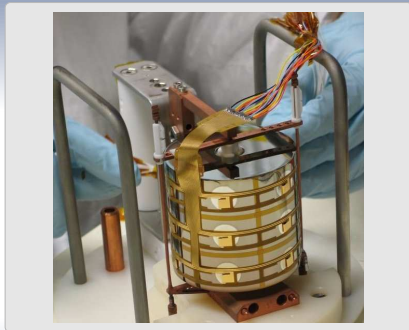
Single-segment



Multi-segment



Segmented germanium detectors



Siegfried-II detector:

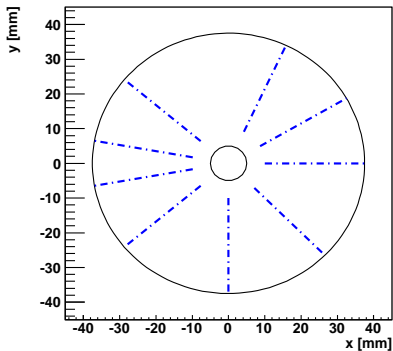
- Diameter 75 mm, height 70 mm;
- $3z \times 6\phi$ -segmentation;
- High-purity:
 $\rho_{\text{imp}} \sim 0.45 \cdot 10^{10} / \text{cm}^3$:
1 ion per $\sim 10^{13}$
germanium ions.
- Operational voltage:
2000 V and higher.



Anisotropy



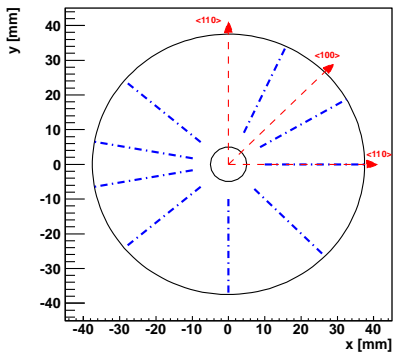
Effect of anisotropy



--- Electrical field lines



Effect of anisotropy

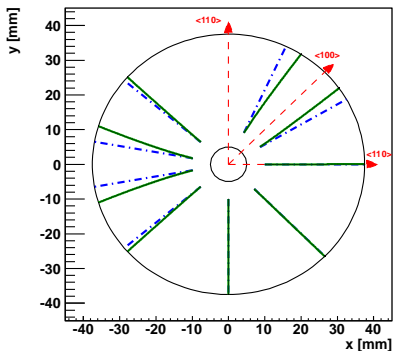





--- Electrical field lines

--- Crystallographic axes



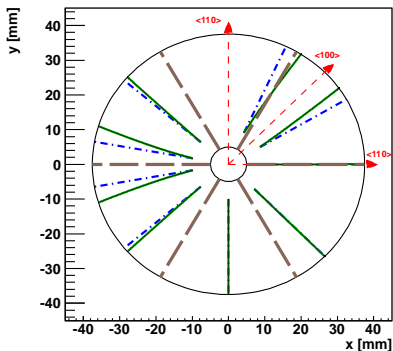
Effect of anisotropy



-  **Electrical field lines**
-  **Crystallographic axes**
-  **Drift trajectories**



Effect of anisotropy



- - - Electrical field lines
- - - Crystallographic axes
- Drift trajectories
- - - Segments



Effect of anisotropy: conclusion

Anisotropy “changes” segmentation!



Effect of anisotropy: conclusion

Anisotropy “changes” segmentation!

Drifting charge cloud of 2 mm at $r = 2.5$ cm
has a spread of 5° .



A bit of theory: mobility

Drift velocity of charge carriers

$$\mathbf{v} = \mu \cdot \mathcal{E}$$

Notations

- \mathbf{v} - Velocity of charge carriers (electrons, holes)
- μ - mobility;
- \mathcal{E} - electrical field;



A bit of theory: mobility

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A bit of theory: mobility

Drift velocity of charge carriers

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Drift component $\perp \mathcal{E}$

$$\mathbf{v}_\phi \neq 0,$$

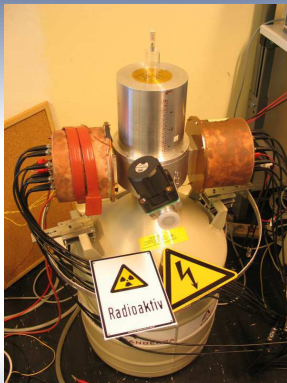
$$\mathbf{v}_\phi = f(v_{\langle 111 \rangle}, v_{\langle 100 \rangle})$$

Notations

- \mathbf{v} - Velocity of charge carriers (electrons, holes)
- μ - mobility;
- \mathcal{E} - electrical field;
- $v_{\langle 111 \rangle}, v_{\langle 100 \rangle}$ - parameters; electron/hole velocities along axes.



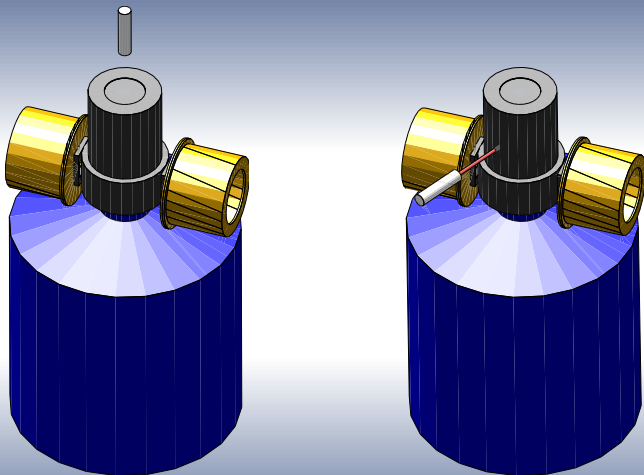
Vacuum cryostat K1



Detector in vacuum cooled through a cooling finger at $T = 90 - 120$ K.

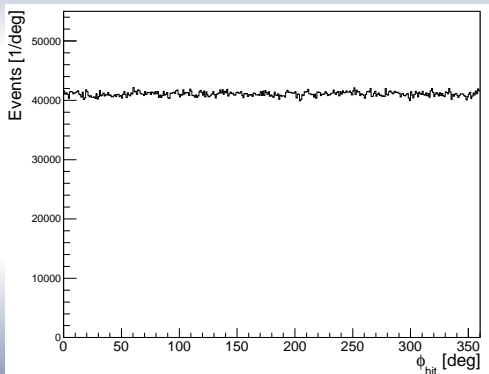
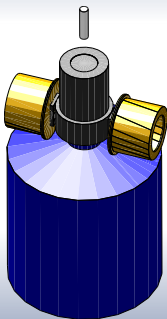


Vacuum cryostat K1 in simulation



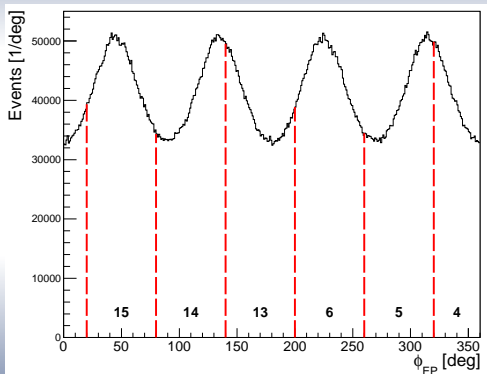
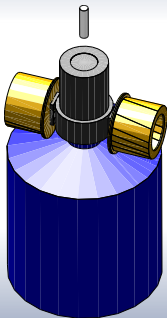
Effect of anisotropy

Energy deposits from a γ source located homogeneous in ϕ ,
Cobalt-60:



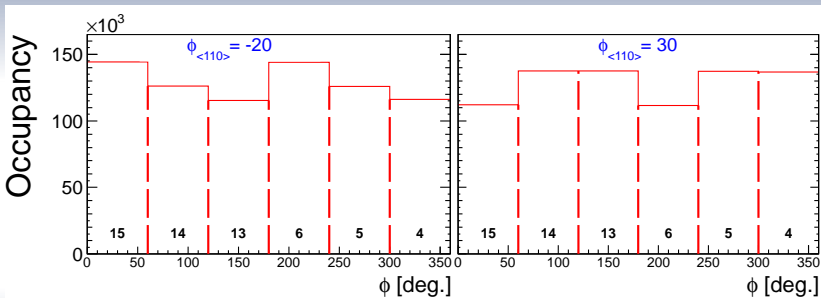
Effect of anisotropy

Charge carriers as they reach the contacts
at the outer surface:



Effect of anisotropy: occupancy

Number of events in segments, 1.33 MeV line, single segment cut:

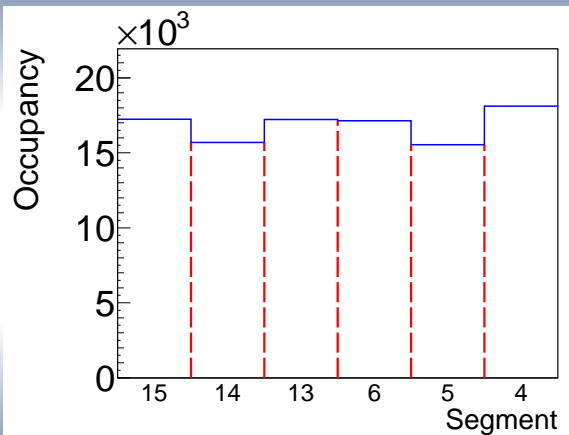


Simulation



Measurements

Number of events in segments, 1.33 MeV line, single segment cut:



Extraction method: idea

- Simulation has a free parameter: axes orientation angle, $\phi_{\langle 110 \rangle}^{sim}$;



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Extraction method: idea

- Simulation has a free parameter: axes orientation angle, $\phi_{\langle 110 \rangle}^{sim}$;
- For varied $\phi_{\langle 110 \rangle}^{sim}$ compare simulated and measured occupancies - a test statistic is needed;
- The best fit gives a hint about axes orientation.

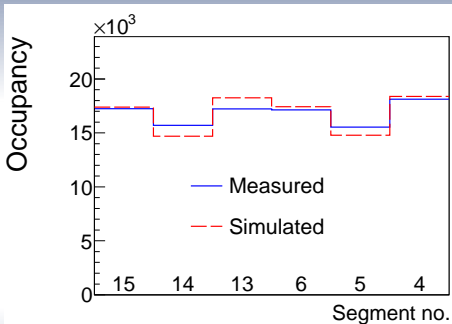


Extraction method: procedure

- 1 Vary $\phi_{\langle 110 \rangle}^{sim}$ in 1° steps;
- 2 For each $\phi_{\langle 110 \rangle}^{sim}$ a **test statistic** ϵ is calculated;
- 3 Dependence of ϵ on $\phi_{\langle 110 \rangle}^{sim}$ is a smooth function;
- 4 $\epsilon \left(\phi_{\langle 110 \rangle}^{sim} \right)$ is fitted with a second order polynomial;
- 5 The minimum of the fit = $\phi_{\langle 110 \rangle}$.



Test statistic



Test statistic

$$\sum_{\text{segments}} \frac{(\text{Data}_i - \text{MC}_i)^2}{\text{Data}_i^2}$$



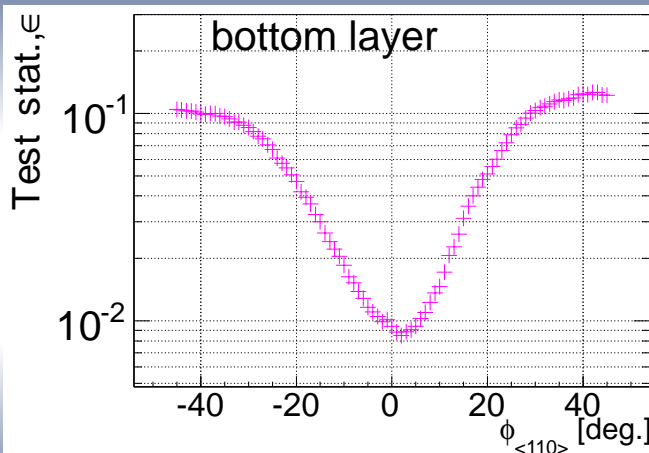
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$\Delta x \Delta y \geq \hbar$

Dependence of ϵ on angle parameter $\phi_{\langle 110 \rangle}^{sim}$

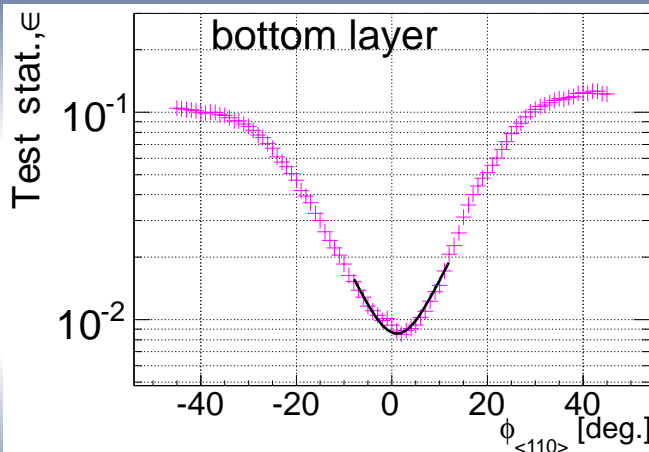


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Fit on test statistic



Results and comparison

Method	Value [degree]
True value *	$\phi_{\langle 110 \rangle} = -0.2^\circ \pm 0.4^\circ (\text{stat.}) \pm 3^\circ (\text{syst.})$
Source on top	$\phi_{\langle 110 \rangle}^{\text{top}} = -1.8^\circ \pm 1^\circ (\text{stat.}) \pm 6^\circ (\text{syst.})$
Source at the side **	$\phi_{\langle 110 \rangle}^{\text{side}} = -11.5^\circ \pm 3^\circ (\text{stat.}) \pm 7^\circ (\text{syst.})$

* Obtained using a reference method

** The source was misaligned by $\approx 5^\circ$



Extraction method: variations

- Various alternatives may have different qualities of the result:



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- Various alternatives may have different qualities of the result:
 - Different layers of the detector (top, middle, bottom);
 - Different lines of a source:
 - 1 ^{60}Co : 1.17 MeV; 1.13 MeV;
 - 2 ^{208}Tl : 0.58 MeV; 2.61 MeV;
 - Different source positions: top, side.



Extraction method: variations

- Various alternatives may have different qualities of the result:
 - Different layers of the detector (top, middle, bottom);
 - Different lines of a source:
 - ① ^{60}Co : 1.17 MeV; 1.13 MeV;
 - ② ^{208}Tl : 0.58 MeV; 2.61 MeV;
 - Different source positions: top, side.
- Cobalt lines, 1.17 MeV and 1.33 MeV seem to be best suited:
 - ① High probability of emission from the source;
 - ② High enough probability to be fully absorbed in a single segment.



Summary

- In some cases a precise knowledge of the crystallographic axes orientation in a Ge-detector is required
- A new method to determine the axes orientation was developed and tested



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- In some cases a precise knowledge of the crystallographic axes orientation in a Ge-detector is required
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- Very sensitive to any imperfection of setup representation in simulation
- The more data is available, the better: enough data is required to get satisfactory accuracy



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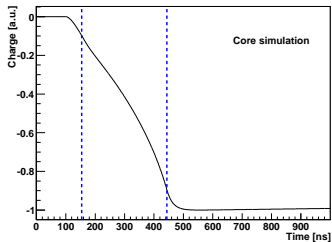
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- A new method to determine the axes orientation was developed and tested
- Very sensitive to any imperfection of setup representation in simulation
- The more data is available, the better: enough data is required to get satisfactory accuracy
- No need to move the source, wait and see: **much faster** than the reference ϕ -scanning method



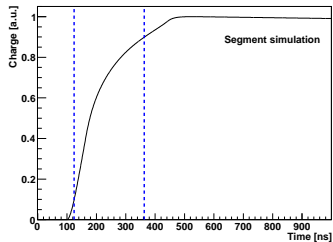
Backup



Simulated pulse



Core pulse



Segment pulse

Pulse length as function of source position

